

M63028/029FP

Spindle Motor and 5ch Actuator Driver

REJ03F0024-0100Z Rev.1.0 Sep.16.2003

Features

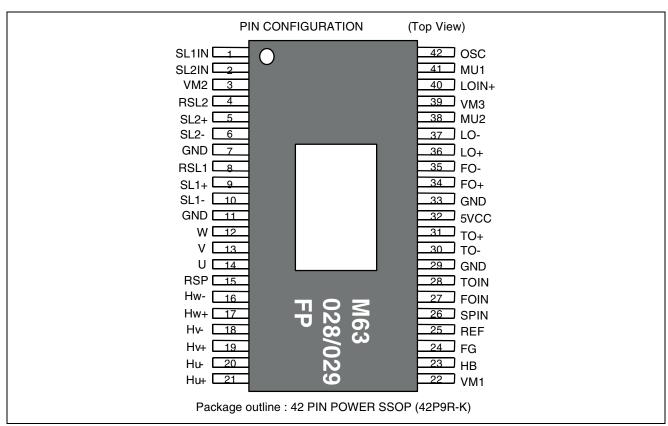
This IC is 1 chip driver IC for spindle motor and 5 channel actuators. All of the motor and actuator of optical disk drive system (CD- ROM etc.) can be drived by only this IC.

This IC has a direct PWM control system for Spindle and Slide channels drive due to reducing IC power dissipation.

This IC has four voltage supply terminals (for Spindle, Slide, Focus/Tracking and Loading), and four voltage supply can be set separately.

Further more this IC has short braking select function, FG amplifier, thermal shut down circuit, standby circuit, reverse rotation detect circuit.

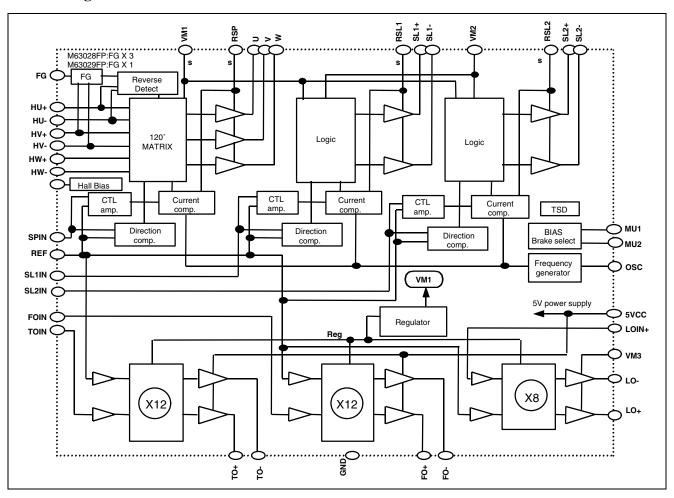
Pin Configuration



Application

CD- ROM, CD- R/RW, DVD, DVD- ROM, DVD- RAM, Optical disc related system, etc

Block Diagram



M63028/029FP

Pin Function

Terminal	Symbol	Terminal Function	Terminal	Symbol	Terminal Function
1	SL1IN	Slide control voltage input 1	42	OSC	PWM carrier oscilation set
2	SL2IN	Slide control voltage input 2	41	MU1	mute/break select terminal 1
3	VM2	Motor Power Supply 2 (for Slide)	40	LO N+	Loading control input (+)
4	RSL2	Slide current sense 2	39	VM3	Power Supply3(for Loading)
5	SL2+	Slide non-inverted output 2	38	MU2	mute/break select terminal 2
6	SL2-	Slide inverted output 2	37	LO-	Loading inverted output
7	GND	GND	36	LO+	Loading non-inverted output
8	RSL1	Slide current sense 1	35	FO-	Focus inverted output
9	SL1+	Slide non-inverted output 1	34	FO+	Focus non-inverted output
10	SL1-	Slide inverted output 1	33	GND	GND
11	GND	GND	32	5VCC	5V Power Supply (for FS, TS)
12	W	Motor drive output W	31	TO+	Tracking non-inverted output
13	V	Motor drive output V	30	TO-	Tracking inverted output
14	U	Motor drive output U	29	GND	GND
15	RSP	Spindle current sense	28	TO N	Tracking control voltage input
16	HW-	HW- sensor amp.input	27	FO N	Focus control voltage input
17	HW+	HW+ sensor amp.input	26	SP N	Spindle control voltage input
18	HV-	HV- sensor amp. input	25	REF	Reference voltage input
19	HV+	HV+ sensor amp. input	24	FG	Frequency generator output
20	HU-	HU- sensor amp. input	23	НВ	Bias for Hall Sensor
21	HU+	HU+ sensor amp. input	22	VM1	Motor Power Supply 1 (for Spindle)

Function

	FO, TO Gain	LO Gain	FG Pulse	
M63028FP	12V/V	8V/V	×3	
M63029FP	12V/V	8V/V	×1	

Absolute Maximum Rating (Ta=25°C)

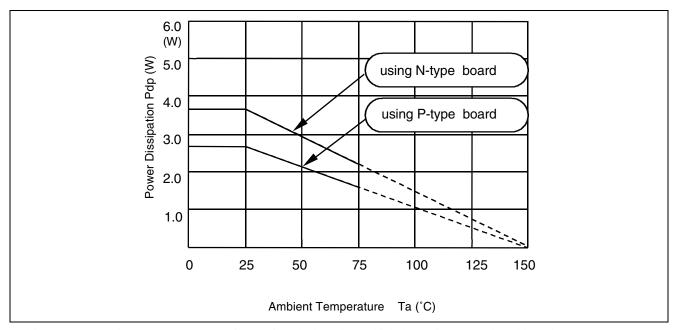
Symbol	Parameter	Conditions	Rating	Unit	
5VCC	5V Power Supply	Focus and Tracking power supply	7	V	
VM1	Motor power Supply 1 *note1	Spindle power supply *note1	15	V	
VM2	Motor power Supply 2	Slide power supply	15	V	
VM3	Motor power Supply 3	Loading power supply	15	V	
IoA	Motor Output Current A	Focus, Tracking and Loading output current *note1	1.0	А	
loB	Motor Output Current B	Spindle output current *note1	1.5	А	
loC	Motor Output Current C	Slide output current *note1	0.5	А	
Vin	Maximum input voltage of terminals	MU1, Hw-, Hw+, Hv-, Hv+, Hu-, Hu+, REF, SPIN, MU2, TOIN, FOIN, OSC, SL1IN, SL2IN, LOIN+	0 to 5VCC	V	
Pt	Power dissipation	70mm X 70mm X 1.6mm Free Air and on the grass epoxy board	2.6	W	
Κθ	Thermal derating	70mm X 70mm X 1.6mm Free Air and on the grass epoxy board	20.8	mW/°C	
Tj	Junction temperature		150	°C	
Topr	Operating temperature		-20 to +75	°C	
Tstg	Storage temperature		-40 to +150	°C	

Note: 1. The ICs must be operated within the Pt (power dissipation) or the area of safety operation.

Recommended Operating Conditions ($Ta = 25^{\circ}C$)

LIMITS Symbol Unit **Parameter** Minimum Maximum **Typical** ٧ VM1 VM1 power supply (for Spindle) 7.5 12 13.2 VM2 ٧ VM2 power supply (for Slide) 4.5 12 13.2 VM3 ٧ VM3 power supply (for Loading) 4.5 12 13.2 5VCC 5V power supply (for FS, TS) 4.5 5 7 ٧ loΑ Focus, Tracking and Loading Output Current 0.5 8.0 Α IoB Spindle Output Current 0.5 1 Α loC Slide Output Current 0.25 0.4 Α Fosc PWM carrier frequency 30 120 kHz

Thermal Derating



This IC's package is POWER-SSOP, so improving the board on which the IC is mounted enables a large power dissipation without a heat sink.

For example, using an 1 layer glass epoxy resin board, the IC's power dissipation is 2.6W at least. And it comes to 3.6W by using an improved 2 layer board.

The information of the N, P type board is shown in attached.

Electrical Characteristics

Common

(Ta=25°C, 5VCC=VM3=5V, VM1 = VM2 = 12V unless otherwise noted.)

Limits						
Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
lcc1	Supply current	5VCC, VM1, VM2, VM3 current	_	32	42	mA
lcc2	Sleep current	5VCC, VM1, VM2, VM3 current under Sleep (MU1 = MU2 = 0V)	_	0	30	μΑ
Fosc	PWM carrier frequency	OSC: with 330pF	_	65	_	kHz
VinREF	REF inout voltage range		1.0	_	3.3	V
linREF	REF terminal input current	VREF = 1.65V	-10	_	10	μΑ
VMU1LO	MUTE1 terminal low voltage	MU1	_	_	0.8	V
VMU1HI	MUTE1 terminal high voltage	MU1	2.5	_	_	V
IM1U	MUTE1 terminal input current	MU1 at 5V input voltage	_	_	500	μΑ
VMU2LO	MUTE2 terminal low voltage	MU2	_	_	0.8	V
VMU2HI	MUTE2 terminal high voltage	MU2	2.5	_	_	V
IM2U	MUTE2 terminal input current	MU2 at 5V input voltage	_	_	500	μΑ

Electrical Characteristics

Spindle

 $(Ta=25^{\circ}C, 5VCC = VM3 = 5V, VM1 = VM2 = 12V \text{ unless otherwise noted.})$

			LIMITS			
Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
Vdyc1	Dynamic range of output	lo = 0.5 [A]	10.6	11.1	_	V
Vdead1-	Control voltage dead zone 1	SPIN <ref [REVERSE]</ref 	-80	-40	0	mV
Vdead1+		REF <spin [FORWARD]</spin 	0	+40	+80	mV
Vin1	Control voltage input range 1	SPIN	0	_	5	V
Gvo1	Control gain 1	Gio1 = Gvo1 / Rs [A/V]	0.85	1.0	1.15	V/V
Vlim1F	Control limit 1F	Ilim1F = Vlim1F / Rs [A] [FORWARD] at MU2 = 0V	0.4	0.5	0.6	V
Vlim2F	Control limit 2F	Ilim1F = Vlim2F / Rs [A] [FORWARD] at MU2 = 5V	0.22	0.28	0.34	V
Vlim1R	Control limit 1R	Ilim1R=Vlim1R / Rs[A] [REVERSE]	0.22	0.28	0.34	V
VHcom	Hall sensor amp. common mode input range	Hu+, Hu-, Hv+, Hv-, Hw+, Hw-	1.3	_	3.7	V
VHmin	Hall sensor amp. input signal level	Hu+, Hu–, Hv+, Hv–, Hw+, Hw–	60	_	_	mVp–p
VHB	HB output voltage	at Load current (IHB) = 10mA	0.6	0.85	1.2	V
IHB	HB terminal sink current	MU1 = 5V	_	_	30	mA

Slide1, 2

 $(Ta=25^{\circ}C, 5VCC = VM3 = 5V^{\circ}C, VM1 = VM2 = 12V \text{ unless otherwise noted.})$

			Limits				
Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit	
Vdyc2	Dynamic range of output	Io = 0.5 [A] at VM2 = 5 [V] RSL = 0.9Ω	3.75	3.95	-	V	
		lo = 0.5 [A] at VM2 = 12 [V]	10.3	10.8	-	_	
Vdead2-	Control voltage dead	SL1IN, SL2IN <ref< td=""><td>-80</td><td>-40</td><td>0</td><td>mV</td></ref<>	-80	-40	0	mV	
Vdead2+	zone 2	REF <sl1in, sl2in<="" td=""><td>0</td><td>+40</td><td>+80</td><td>mV</td></sl1in,>	0	+40	+80	mV	
Vin2	Control voltage input range 2	SL1IN, SL2IN	0	-	5	V	
Gvo2	Control gain 2	Gio2 = Gvo2 / Rs [A/V]	0.85	1.0	1.15	V/V	
Vlim2	Control limit 2	Ilim2 = Vlim2 / Rs [A]	0.43	0.5	0.58	V	
Tdon	Output turn-on delay		-	1.0	2.0	μS	
Tdoff	Output turn-off delay		-	2.0	3.5	μS	
Tdsw	Output switching delay		-	3.0	6.0	μS	
lleak	Output leak current	MU1=MU2=0V	-100	-	100	μА	

Electrical Characteristics

Loadhing

 $(Ta=25^{\circ}C, 5VCC = VM3 = 5V, VM1 = VM2 = 12V \text{ unless otherwise noted.})$

			Limits			
Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
Vdyc3-1	Dynamic range of	VM1 = 12[V	3.95	4.2	-	V
	output	VM3 = 5[V] Io = 0.5A				
		VM1 = 12[V]	6.9	7.6	-	_
		VM3 = 12[V] Io = 0.5A				
Vdyc3-2	Dynamic range of	R=5.4[Ω]	3.35	3.55	-	V
	output	VM3 = 4.75V, VM1 = 12V				
Vin3	Control voltage input	LOUN+	0	-	5	V
	range 3					
Gvo3	Control gain 3	(LO+) - (LO-)	16.7	18.1	19.3	dB
		(LOIN+) – (REF)				
Voff1	Output offset voltage	(LO+) - (LO-)	-50	0	+50	mV
		at LOIN+ = REF = $1.65V$				

Focus

 $(Ta=25^{\circ}C, 5VCC = VM3 = 5V, VM1 = VM2 = 12V \text{ unless otherwise noted.})$

Symbol	Parameter	Conditions		Limits Minimum	Typical	Maximum	Unit
Vdyc4	Dynamic range of	VM1 = 12[V]	lo = 0.5[A]	4.0	4.25	-	V
	output	VM1 = 12[V]	lo = 0.8[A]	3.55	3.95	-	_
Vin4	Control voltage input range 4	FOIN, TOIN		0	-	5	V
Gvo4	Control gain 4	(FO+) – (FO–) FOIN – REF	(TO+) - (TO-) TOIN - REF	20.2	21.6	22.8	dB
Voff2	Output offset voltage	(FO+) - (FO-) a = 1.65V (TO+) - (TO-) a = 1.65V		-30	0	+30	mV

NOTE: This IC need condenser between each supply lines and GND for stopped Oscillation.

Thermal Characteristics

		Function Start Temperature of IC			Function Start Temperature of IC			
Symbol	Parameter	Minimum	Typical	Max	Minimum	Typical	Max	Unit
TSD	Thermal Shut Down *note3	-	165	-	-	130	-	°C

^{*}note3 This TSD function start temperature doesn't show the guaranteed max. temperature of the devices.

The guranteed max.temperature is Tjmax.which is shown in "9.ABSOLUTE MAXIMUM RATING". The TSD function is a thermal protection in case the temperature of the devices goes up above Tjmax because of wrong use.

And these TSD temperature are the target temperatures for circuit design, not the guranteed temperatures. (The TSD function of all the devices is not checked by a test in high temperature.)



Channel Select Function

	Logic control			Drive chan	Drive channel					SPIN <ref< th=""><th>SPIN>REF</th></ref<>	SPIN>REF
	MU1	MU2	SPIN	Loading	Slide1	Slide2	Focus	Tracking	Spindle	Curren limit	Currentlim it (Brake select)
SELECT 6	Н	Н	Н	Off	On	On	On	On	On	56%	
SELECT 5	Н	L	Н	Off	On	On	On	On	On	100%	
SELECT 4	Н	Н	L	Off	On	On	On	On	On		56% (PWM)
SELECT 3	Н	L	L	Off	On	On	On	On	On		(Short)
SELECT 2	L	Н		On	Off	Off	Off	Off	Off		
SELECT 1	L	L		Off	Off	Off	Off	Off	Off		

This IC has two MUTE terminal (MU1 and MU2).

It is possible to control ON / OFF of each channel and to select current limit under acceleration by external logic inputs.

It has six kinds of function for select.In case of SELECT1, the bias of all circuit becomes OFF.

Therefore, this mode is available in order to reduce the power dissipation when the waiting mode.

In case of SELECT2, the bias of other than Loading circuit becomes OFF.

Therefore, this mode is available in order to reduce the power dissipation when the active mode.

In case of SELECT3, it is possible to select the short braking to take the brake of Spindle motor. in case of SELECT4, it is possible to select PWM reverse braking when in the same.

In case of SELECT5, it is possible to select the 100% current limit under acceleration.

Also,in case of SELECT6,it is possible to select the 56% current limit under acceleration.

Therefore, this mode is available in order to reduce a temperature under acceleration.

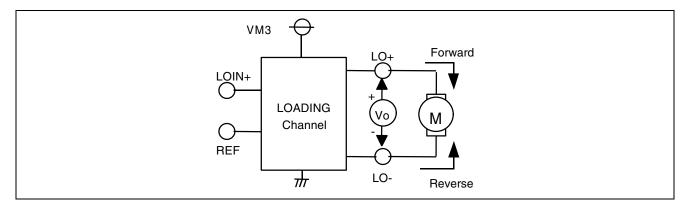
Loading channel

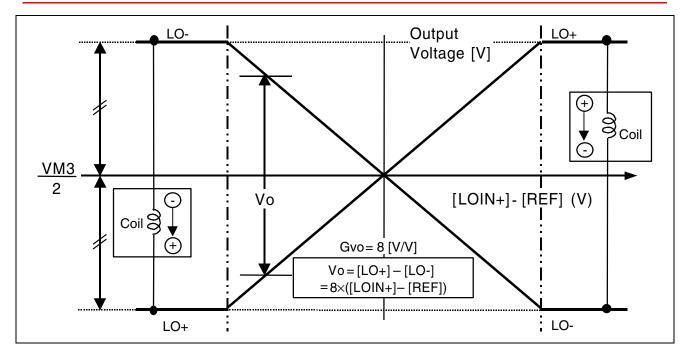
The loading channel is the circuit of BTL voltage drive. This circuit has

the referential input. Output swing is determined with ΔV in X 8. Also, it is possible for this channel to use for the slide motor, the focus coil and the tracking coil.

The input terminal is high impedance. It is possible to do variable a gain by external resistor.

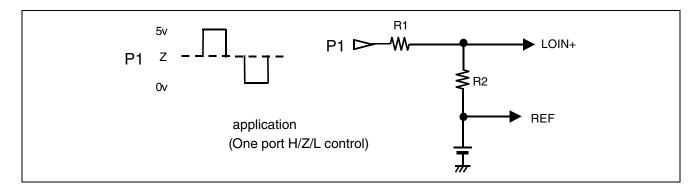
In case of one MCU port, if use three state port, it is possible for this channel to have the stop function.





application (MCU: One port H/Z/L control)

Logic contorol P1	Situation of loading channnel	Output voltage swing
5V	Forward rotation	$Vo = 8 \times (5[V]-REF[V]) \times R2/(R1+R2)$
Z (Hi impedance)	Short brake>Stop	Vo=0[V]
0	Reverse rotation	$Vo = -8 \times (0[V]-REF[V]) \times R2/(R1+R2)$



Spindle channel

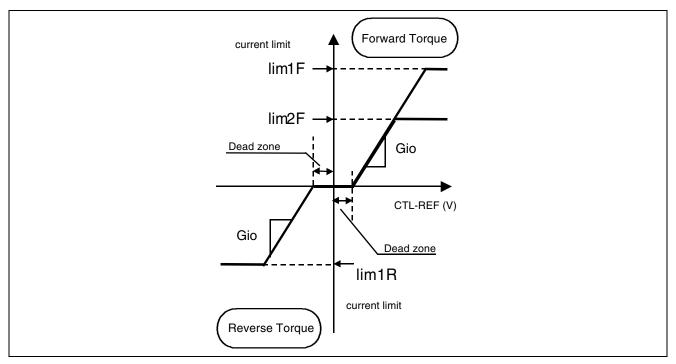
The relationship between the differential voltage between SPIN and REF and the torque is shown in following Figure. The voltage gain[Gvo] is 1.0 [V/V].

The current gain [Gio] is 2.0 [A/V] (at sensing resistor :0.5 Ω ,and R1= ∞ , R2=0 Ω) in forward torque directions,and the dead zone is from 0mV to 80mV (at R1= ∞ , R2=0 Ω)

The coil current gain under the reverse torque is the same with in forward torque directions. And the limitation function gets on when the differential voltage of VM1(12V) to RSP is 0.5V at forward and 0.28V at reverse.

In case of SELECT6 the differential voltage of VM1(12V)~RSP is 0.28V at forward. Therefore, this mode is available in order to reduce a temperature under acceleration.

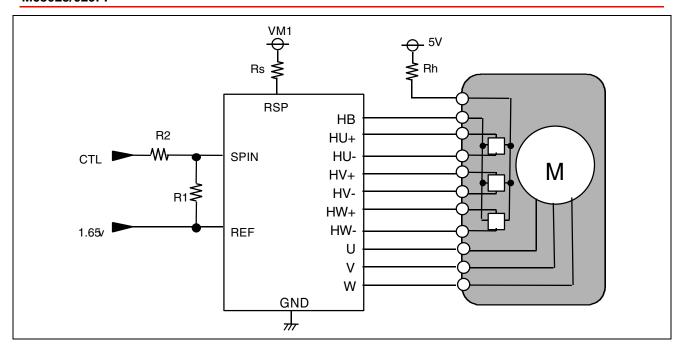
Therefore current- gain- control and current- limit of this IC is determined with sensing resister value, and more detail control can be determined with setting a gain- resister outer this IC as below.



The example of current- gain and current- limit of SPINDLE.

				Gio*[A/V]				
Rs[Ω]	llim1F[A]	llim2F[A]	llim1R[A]	$R1 = \infty R2 = 0\Omega$	R1 = R2	R2 = 2•R1		
0.50	1.00	0.56	0.56	2.00	1.00	0.66		
0.75	0.66	0.37	0.37	1.33	0.66	0.44		
1.00	0.50	0.28	0.28	1.00	0.50	0.33		

 $Gio^* = R1/[(R1+R2) \cdot Rs][A/V]$

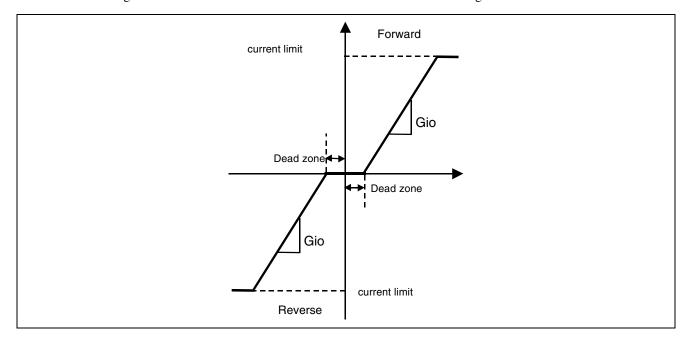


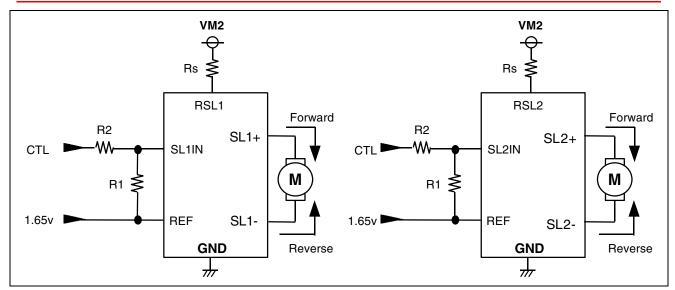
Slide channel

The relationship between the differential voltage between SLIN and REF and the torque is shown in following Figure. The voltage gain[Gvo] is 1.0 [V/V]. The current gain is 2.0[A/V] (at sensing resistor : 0.5Ω and R1= ∞ , R2= 0Ω) in forward torque directions, and the dead zone is from 0mV to 80mV (at R1= ∞ , R2= 0Ω)).

The coil current gain under the reverse torque is the same with in forward torque directions. And the limitation function gets on when the differential voltage of VM2(12V) to RSL is 0.5V.

Therefore current-gain-control and current-limit of this IC is determined with sensing resister value.





The example of current-gain and current-limit of SLIDE.

Gio*[A/V] $\mathsf{Rs}[\Omega]$ llim[A] $R1 = \infty R2 = 0 \Omega$ R1 = R2 R2 = 2•R1 0.50 1.00 2.00 1.00 0.66 0.75 0.66 1.33 0.66 0.44 1.00 0.50 1.00 0.50 0.33

 $Gio^* = R1/[(R1+R2) \cdot Rs] [A/V]$

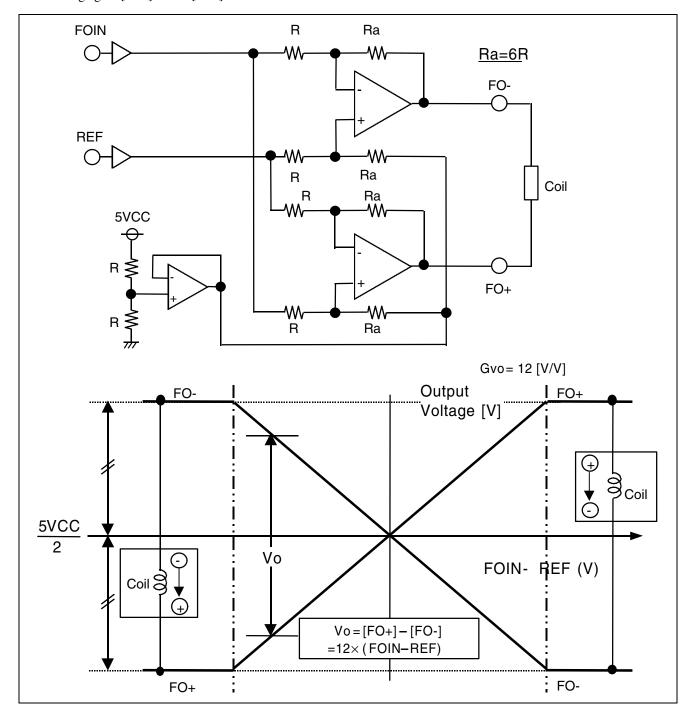
Focus/Tracking channel

The focus and tracking channel is the voltage control drive using BTL.

The focus and tracking is the same composition.

The relationship between the differential voltage between FOIN and REF and the output voltage is shown in following Figure.

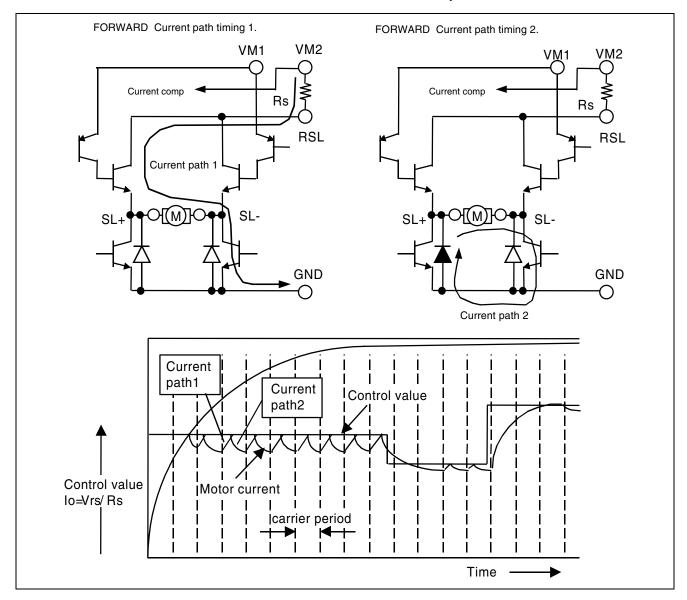
The voltage gain [Gvo] is 12.0[V/V].



Direct PWM operation

The spindle and the slide channel is controlled by the direct PWM control.

Also, built-in the current limit circuit. This IC controls the motor current directly.



PWM carrier frequency setting

PWM carrier frequency is decided by charging and discharging the capacitor that is connected to OSC terminal outer IC.Examination of the relationship the capacitor connected to OSC terminal and PWM carrier frequency is given in following table.

Capacitor [pF]	820	750	330	220	180	130	110
Carrier Frequency [kHz]	28	30	65	90	110	140	160

^{*}note) This PWM carrier frequency is TYP value.

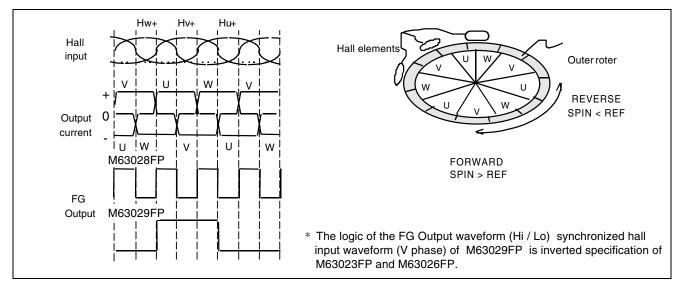
Recommendation of Short Brake Mode at Spindle Drive

This IC has two brake mode, PWM-BRAKE-MODE and SHORT-BRAKE-MODE. In this IC recommendation, SHORT-BRAKE-MODE is superior to PWM-BRAKE- MODE to reducing the power dissipation and to avoid braking down of this IC.

(By excessive reverse torque current in braking a motor with PWM- BRAKE from high- speed- rotation with being excessive Back-EMF, this IC could be broken.)

The relationship between hall-amplifier-input and output-current-commutation/FG output at Spindle Drive

The relationship between the hall elements and the motor output current/FG output is shown in bellow Figure.



FG function at Spindle Drive

The FG terminal outputs the square pulse signal synchronizing with the Hall inputs timing.

And, the FG terminal is open-collector output.

Phase delay circuit at Slide

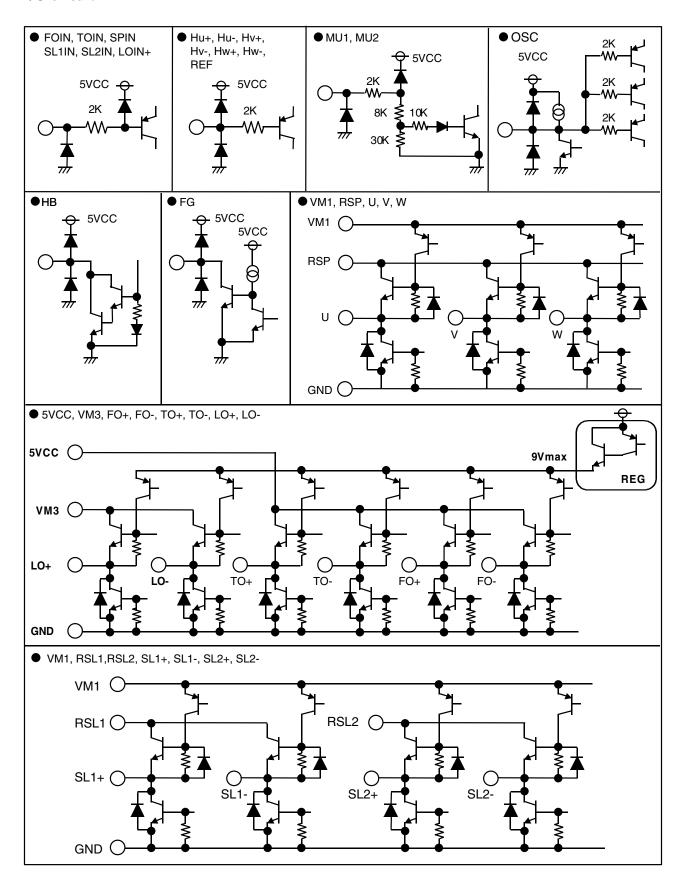
Phase delay circuit is built in the IC to detect an output spike current, when the motor current direction is switching. In switching the motor current direction, Phase delay circuit switch-off all output transistor of H-bridge for 3 µsec.

Output current setting at Slide

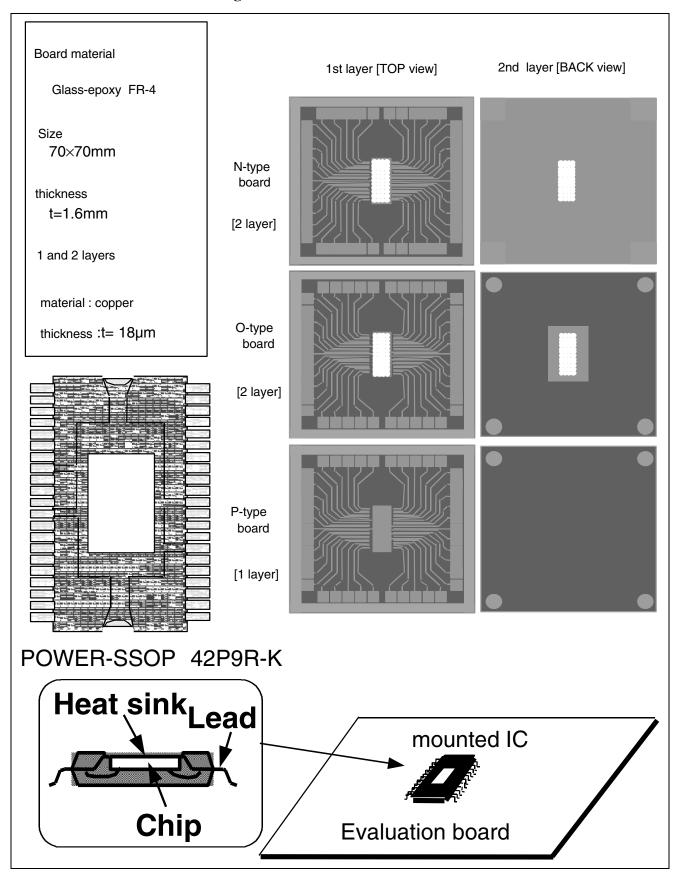
In this IC, since output transistor is NPN- type transistor, motor coil current (Io) is larger than sensing resistance current about 10mA (TYP.) according to base current of output transistor.

Therefore please design output current with consisting these base current.

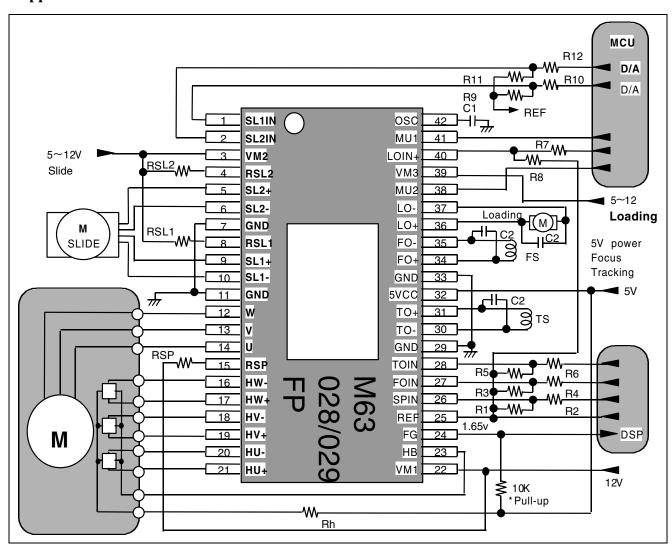
I/O circuit



The boards for thermal derating evaluation



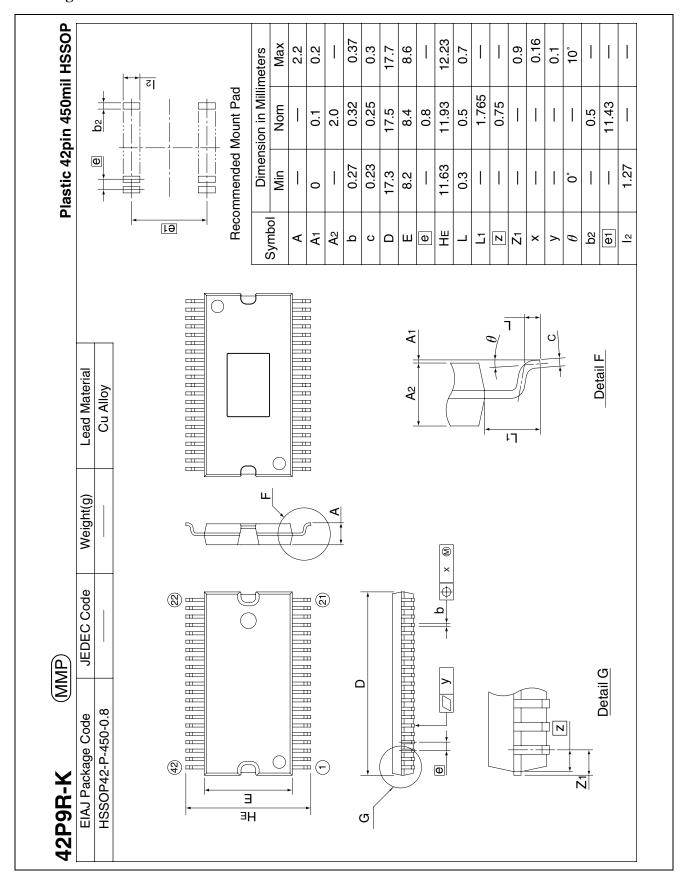
Application Circuit



This value is a recommended value and is not guaranteed performance.

Parts No.	Тур.	Unit	Note
RSP	0.33	Ω	Ilim1F=1.5A, Ilim1R=1.0A, Gain=3.0A/V
RSL1, RSL2	2	Ω	Ilim=0.25A, Gain=0.5A/V
Rh	200	Ω	
R1, R2, R3, R4, R5, R6	10k	Ω	
R7, R8	10k	Ω	
C1	330p	F	Fosc=65kHz
R9, R10, R11, R12	10k	Ω	
C2	100n	F	

Package Dimensions



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